

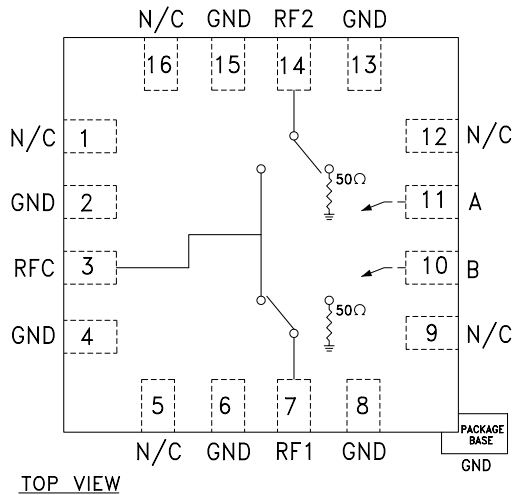
GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 14.0 GHz

Typical Applications

The HMC347LP3 is ideal for:

- Basestation Infrastructure
- Fiber Optics & Broadband Telecom
- Microwave Radio & VSAT
- Military Radios, Radar, & ECM
- Test Instrumentation

Functional Diagram



Features

- High Isolation: >50 dB up to 3 GHz
>45 dB up to 10 GHz
- Low Insertion Loss: 1.6 dB @ 10 GHz
- Non-Reflective Design
- 3 x 3 x 1 mm QFN SMT Package

General Description

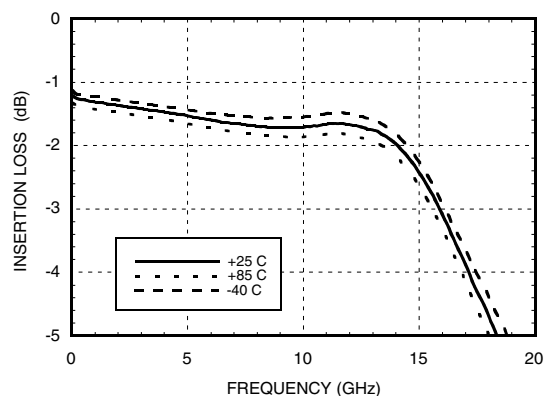
The HMC347LP3 is a broadband high isolation non-reflective GaAs MESFET SPDT switch in a low cost leadless QFN surface mount plastic package. Covering DC to 14 GHz, the switch offers high isolation and low insertion loss. The switch features >50 dB isolation up to 3 GHz and >40 dB isolation up to 13 GHz. The switch operates using complementary negative control voltage logic lines of -5/0V and requires no bias supply. This SPDT is an excellent alternative to the HMC132C8 SPDT.

Electrical Specifications, $T_A = +25^\circ\text{C}$, With 0/-5V Control, 50 Ohm System

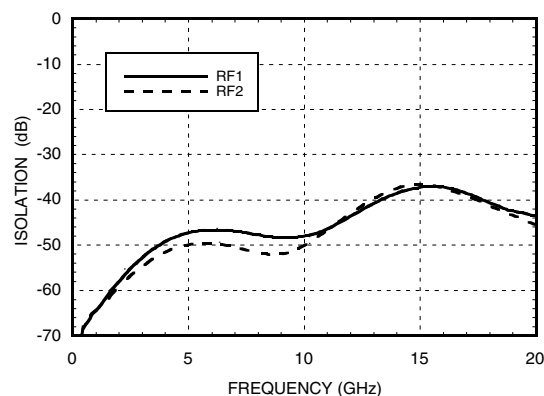
| Parameter | Frequency | Min. | Typ. | Max. | Units |
|---|----------------|----------------------------------|------|------|-------|
| Insertion Loss | DC - 3.0 GHz | | 1.5 | 1.9 | dB |
| | DC - 6.0 GHz | | 1.6 | 2.0 | dB |
| | DC - 12.0 GHz | | 1.6 | 2.1 | dB |
| | DC - 14.0 GHz | | 1.9 | 2.4 | dB |
| Isolation | DC - 3.0 GHz | 49 | 53 | | dB |
| | DC - 6.0 GHz | 41 | 46 | | dB |
| | DC - 12.0 GHz | 39 | 44 | | dB |
| | DC - 14.0 GHz | 33 | 38 | | dB |
| Return Loss | "On State" | DC - 6.0 GHz | 10 | 13 | dB |
| | | DC - 14.0 GHz | 8 | 13 | dB |
| Return Loss RF1, RF2 | "Off State" | DC - 6.0 GHz | 7 | 10 | dB |
| | | DC - 14.0 GHz | 6 | 9 | dB |
| Input Power for 1 dB Compression | 0.5 - 14.0 GHz | 19 | 23 | | dBm |
| Input Third Order Intercept (Two-Tone Input Power= +7 dBm Each Tone) | 0.5 - 14.0 GHz | 38 | 43 | | dBm |
| Switching Characteristics | DC - 14 GHz | tRISE, tFALL (10/90% RF) | 3 | | ns |
| | | tON, tOFF (50% CTL to 10/90% RF) | 6 | | ns |
| | | | | | |

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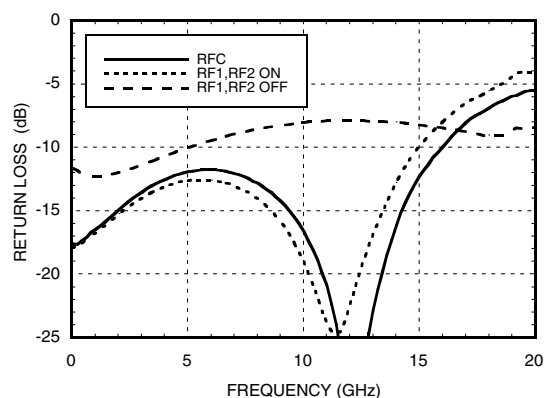
Insertion Loss



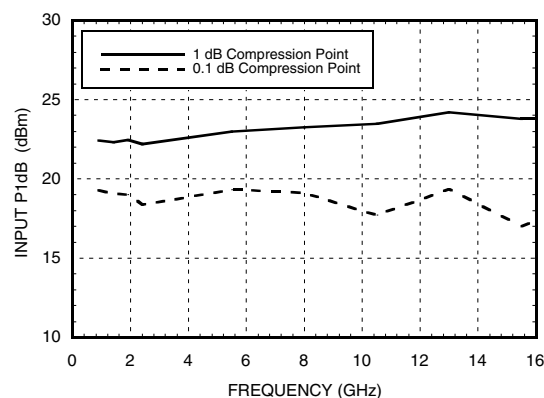
Isolation



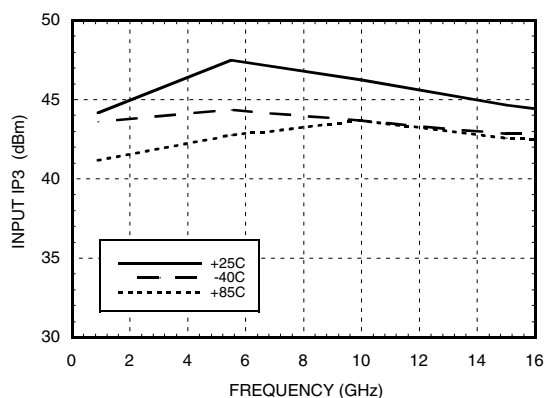
Return Loss



0.1 and 1 dB Input Compression Point



Input Third Order Intercept Point



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Control Voltages

| State | Bias Condition |
|-------|---|
| Low | 0 to -0.2V @ 10 uA Max. |
| High | -5V @ 10 uA Typ. to -7V @ 40 uA Typ. (± 0.5 Vdc) |

Absolute Maximum Ratings

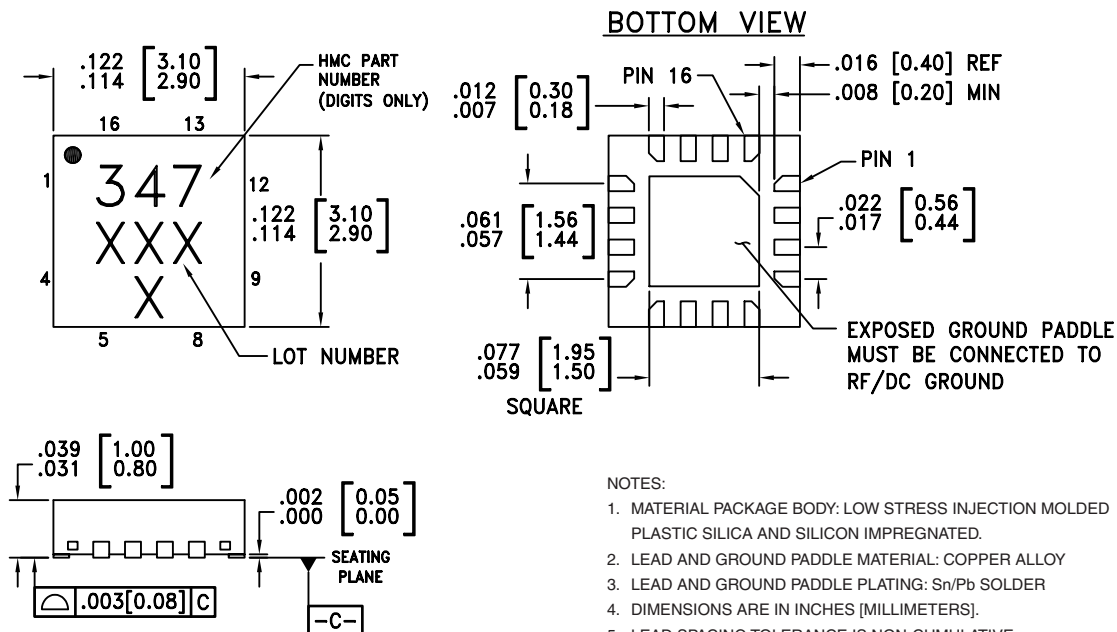
| | |
|--|-------------------|
| RF Input Power ($V_{ctl} = -5V$) | +27 dBm |
| Control Voltage Range (A & B) | +0.5V to -7.5 Vdc |
| Channel Temperature | 150 °C |
| Thermal Resistance (Insertion Loss Path) | 440 °C/W |
| Thermal Resistance (Terminated Path) | 540 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -55 to +85 °C |

Truth Table

| Control Input | | Signal Path State | |
|---------------|------|-------------------|------------|
| A | B | RFC to RF1 | RFC to RF2 |
| High | Low | On | Off |
| Low | High | Off | On |

Caution: Do not "Hot Switch" power levels greater than +13 dBm ($V_{ctl} = 0/-5$ Vdc).

Outline Drawing

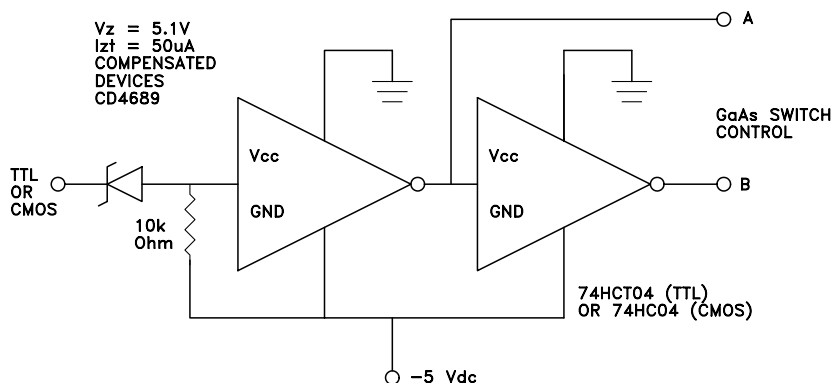


NOTES:


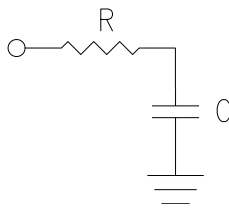
1. MATERIAL PACKAGE BODY: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
2. LEAD AND GROUND PADDLE MATERIAL: COPPER ALLOY
3. LEAD AND GROUND PADDLE PLATING: Sn/Pb SOLDER
4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
5. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
6. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM. PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
7. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
8. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
9. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED PCB LAND PATTERN.

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Suggested Driver Circuit

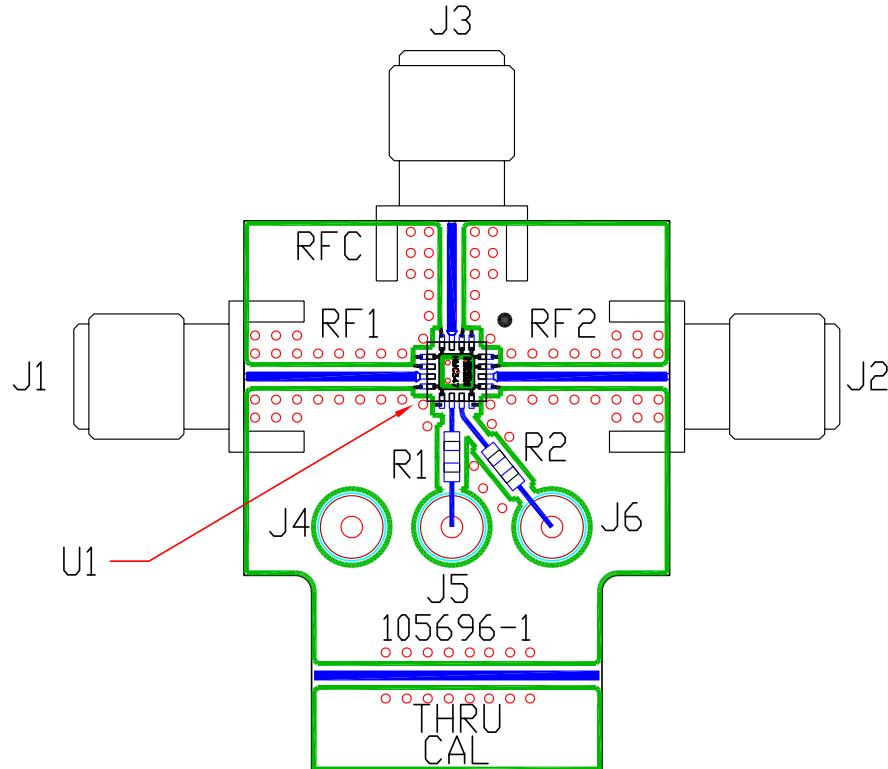


Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|--------------------|---------------|---|---|
| 1, 5, 9, 12, 16 | N/C | This pin should be connected to PCB RF ground to maximize isolation | |
| 2, 4, 6, 8, 13, 15 | GND | Package bottom has exposed metal paddle that must also be connected to PCB RF ground. |  |
| 3, 7, 14 | RFC, RF1, RF2 | This pin is DC coupled and matched to 50 Ohm. Blocking capacitors are required if RF line potential is not equal to 0V. | |
| 10 | CTLB | See truth table and control voltage table. |  |
| 11 | CTLA | See truth table and control voltage table. | |

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Evaluation PCB



List of Material

| Item | Description |
|---------------------------------------|-----------------------------|
| J1 - J3 | PC Mount SMA RF Connector |
| J4 - J6 | DC Pin |
| R1 - R2 | 100 Ohm Resistor, 0603 Pkg. |
| U1 | HMC347LP3 SPDT Switch |
| PCB* | 105696 Evaluation PCB |
| * Circuit Board Material: Rogers 4350 | |

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads and package bottom should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

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Notes: